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FDMT1D3N08B

N-Channel Dual Cool^{TM} 88 PowerTrench® MOSFET

80 V, 164 A, 1.35 mΩ

Features

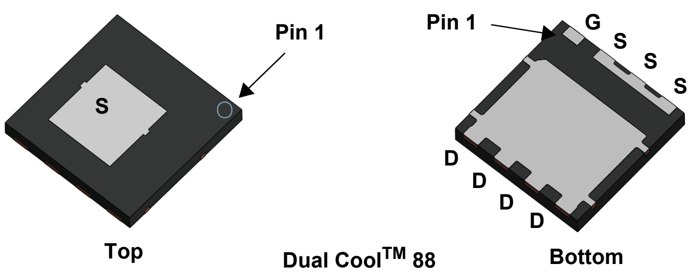
- Max $r_{DS(on)}$ = 1.35 mΩ at V_{GS} = 10 V, I_D = 36 A
- Max $r_{DS(on)}$ = 1.8 mΩ at V_{GS} = 8 V, I_D = 31 A
- Advanced Package and Silicon Combination for Low $r_{DS(on)}$ and High Efficiency
- Next Generation Enhanced Body Diode Technology, Engineered for Soft Recovery
- Low Profile 8x8 mm MLP Package
- MSL1 Robust Package Design
- 100% UIL Tested
- RoHS Compliant

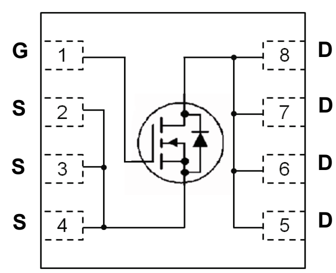
General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process. Advancements in both silicon and Dual Cool^{TM} package technologies have been combined to offer the lowest $r_{DS(on)}$ while maintaining excellent switching performance by extremely low Junction-to-Ambient thermal resistance.

Applications

- OringFET / Load Switching
- Synchronous Rectification
- DC-DC Conversion





MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted.

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			80	V
V_{GS}	Gate to Source Voltage			±20	V
I_D	Drain Current -Continuous	T_C = 25 °C	(Note 5)	164	A
	-Continuous	T_C = 100 °C	(Note 5)	103	
	-Continuous	T_A = 25 °C	(Note 1a)	36	
	-Pulsed		(Note 4)	864	
E_{AS}	Single Pulse Avalanche Energy		(Note 3)	1734	mJ
P_D	Power Dissipation	T_C = 25 °C		178	W
	Power Dissipation	T_A = 25 °C	(Note 1a)	3.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Top Source)	1.9	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Bottom Drain)	0.7	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	38	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1b)	81	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1i)	15	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1j)	21	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1k)	9	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
1D3N08B	FDMT1D3N08B	Dual Cool^{TM} 88	13"	13.3 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units

Off Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	80			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		50		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 64 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±20 V, V_{DS} = 0 V			100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	2.0	3.2	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-11		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 36 A		1.1	1.35	mΩ
		V_{GS} = 8 V, I_D = 31 A		1.3	1.8	
		V_{GS} = 10 V, I_D = 36 A, T_J = 125 °C		1.8	2.2	
g_{FS}	Forward Transconductance	V_{DS} = 5 V, I_D = 36 A		116		S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
C_{iss}	Input Capacitance	V_{DS} = 40 V, V_{GS} = 0 V, f = 1 MHz		14000	19600	pF
C_{oss}	Output Capacitance			2050	2870	pF
C_{rss}	Reverse Transfer Capacitance			50	150	pF
R_g	Gate Resistance		0.1	1.4	2.1	Ω

Switching Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 40 V, I_D = 36 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		63	101	ns
t_r	Rise Time			56	90	ns
$t_{d(off)}$	Turn-Off Delay Time			68	109	ns
t_f	Fall Time			20	32	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 40 V, I_D = 36 A		186	260	nC
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 8 V; V_{DD} = 40 V, I_D = 36 A		152	213	nC
Q_{gs}	Gate to Source Charge	V_{DD} = 40 V, I_D = 36 A		67		nC
Q_{gd}	Gate to Drain “Miller” Charge	V_{DD} = 40 V, I_D = 36 A		37		nC
Q_{oss}	Output Charge	V_{DD} = 40 V, V_{GS} = 0 V		185		nC

Drain-Source Diode Characteristics

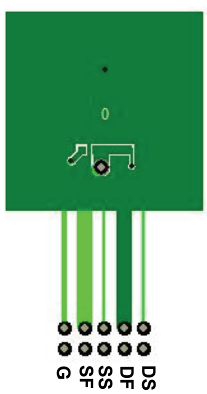
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.6 A (Note 2)		0.7	1.1	V
		V_{GS} = 0 V, I_S = 36 A (Note 2)		0.8	1.2	
t_{rr}	Reverse Recovery Time	I_F = 36 A, di/dt = 100 A/μs		83	132	ns
Q_{rr}	Reverse Recovery Charge			90	143	nC

Thermal Characteristics

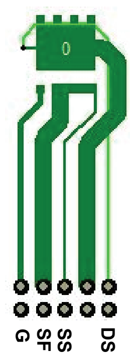
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Top Source)	1.9	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Bottom Drain)	0.7	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1a)	38	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1b)	81	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1c)	26	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1d)	34	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1e)	14	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1f)	16	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1g)	26	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1h)	60	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1i)	15	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1j)	21	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1k)	9	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	(Note 1l)	11	

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a FR-4 board using a specified pad of 2 oz copper as shown below. $R_{\theta CA}$ is determined by the user's board design.



a. 38 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b. 81 °C/W when mounted on a minimum pad of 2 oz copper

c. Still air, 20.9x10.4x12.7mm Aluminum Heat Sink, 1 in^2 pad of 2 oz copper

d. Still air, 20.9x10.4x12.7mm Aluminum Heat Sink, minimum pad of 2 oz copper

e. Still air, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in^2 pad of 2 oz copper

f. Still air, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper

g. 200FPM Airflow, No Heat Sink,1 in^2 pad of 2 oz copper

h. 200FPM Airflow, No Heat Sink, minimum pad of 2 oz copper

i. 200FPM Airflow, 20.9x10.4x12.7mm Aluminum Heat Sink, 1 in^2 pad of 2 oz copper

j. 200FPM Airflow, 20.9x10.4x12.7mm Aluminum Heat Sink, minimum pad of 2 oz copper

k. 200FPM Airflow, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, 1 in^2 pad of 2 oz copper

l. 200FPM Airflow, 45.2x41.4x11.7mm Aavid Thermalloy Part # 10-L41B-11 Heat Sink, minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.
3. E_{AS} of 1734 mJ is based on starting T_J = 25 °C; N-ch: L = 3 mH, I_{AS} = 34 A, V_{DD} = 80 V, V_{GS} =10 V. 100% test at L = 0.3 mH, I_{AS} = 77 A.
4. Pulsed Id please refer to Fig 11 SOA graph for more details.
5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics T_J = 25 °C unless otherwise noted.

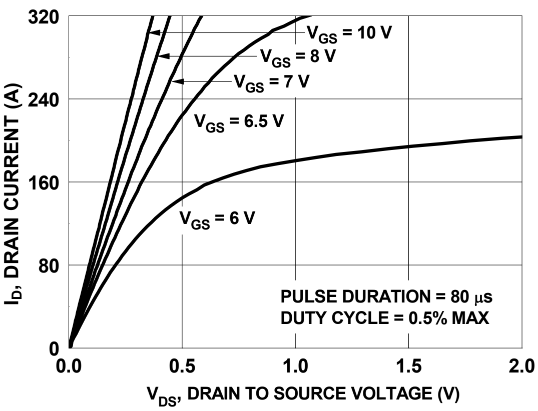


Figure 1. On Region Characteristics

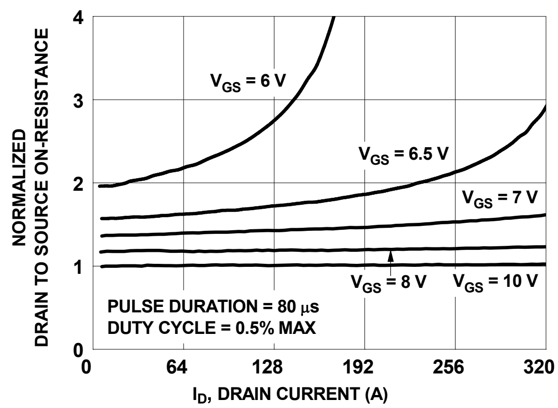


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

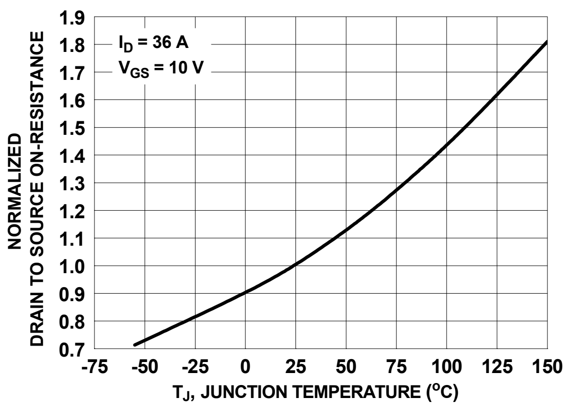


Figure 3. Normalized On Resistance vs. Junction Temperature

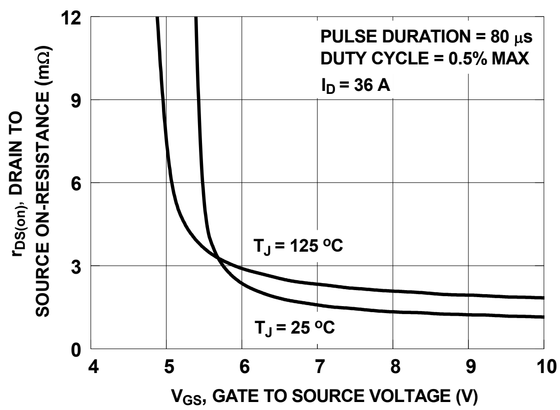


Figure 4. On-Resistance vs. Gate to Source Voltage

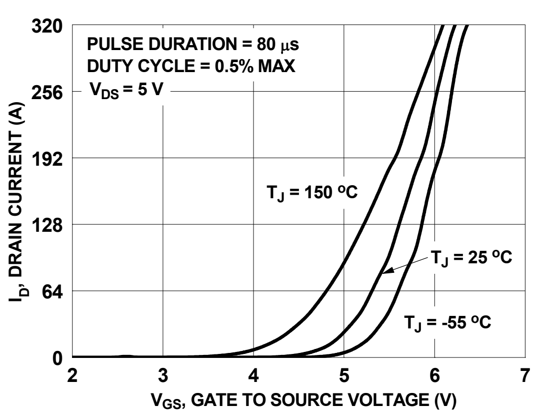


Figure 5. Transfer Characteristics

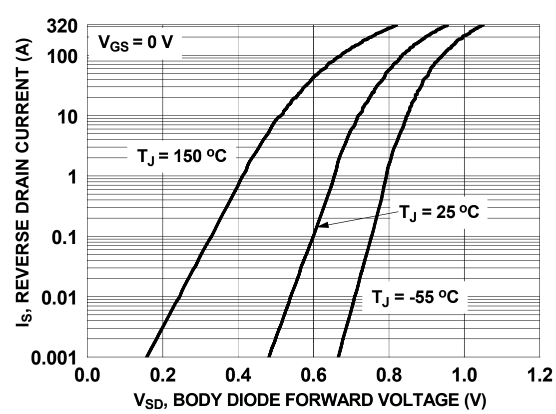


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted.

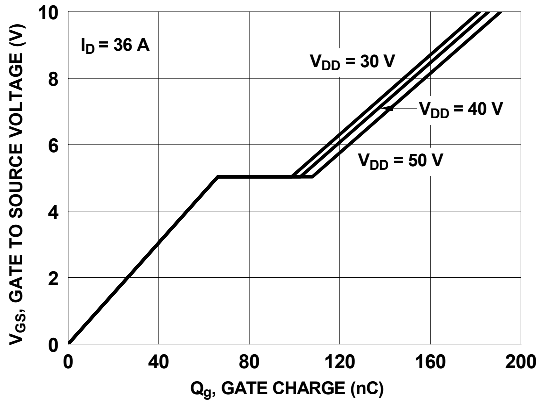


Figure 7. Gate Charge Characteristics

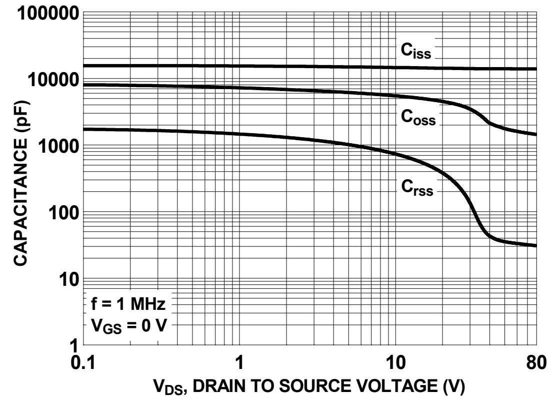


Figure 8. Capacitance vs. Drain to Source Voltage

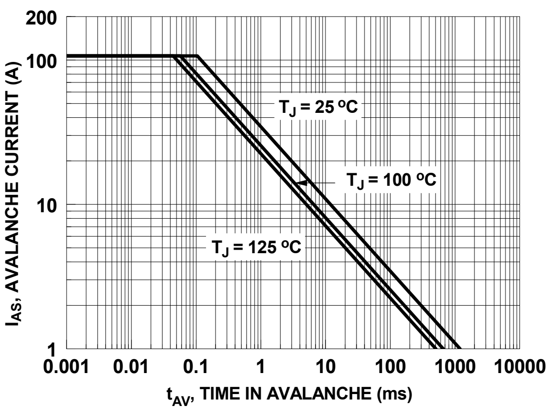


Figure 9. Unclamped Inductive Switching Capability

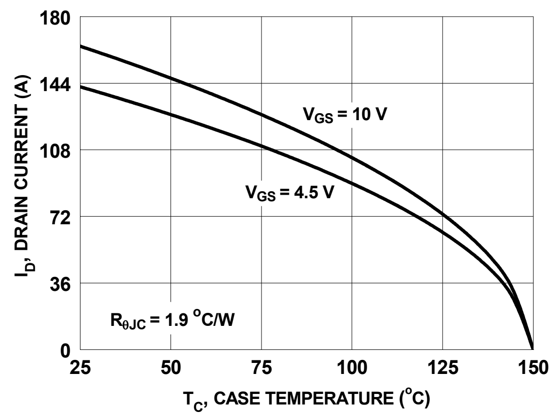


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

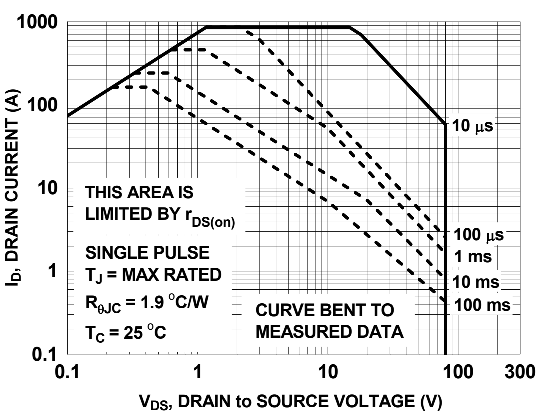


Figure 11. Forward Bias Safe Operating Area

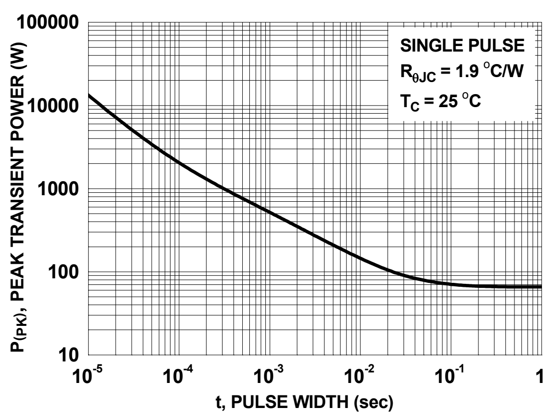


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted.

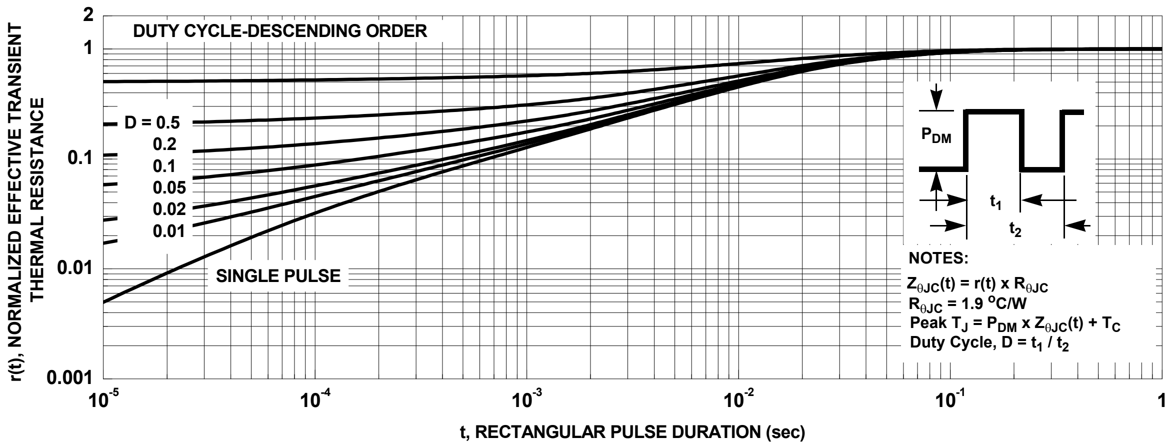
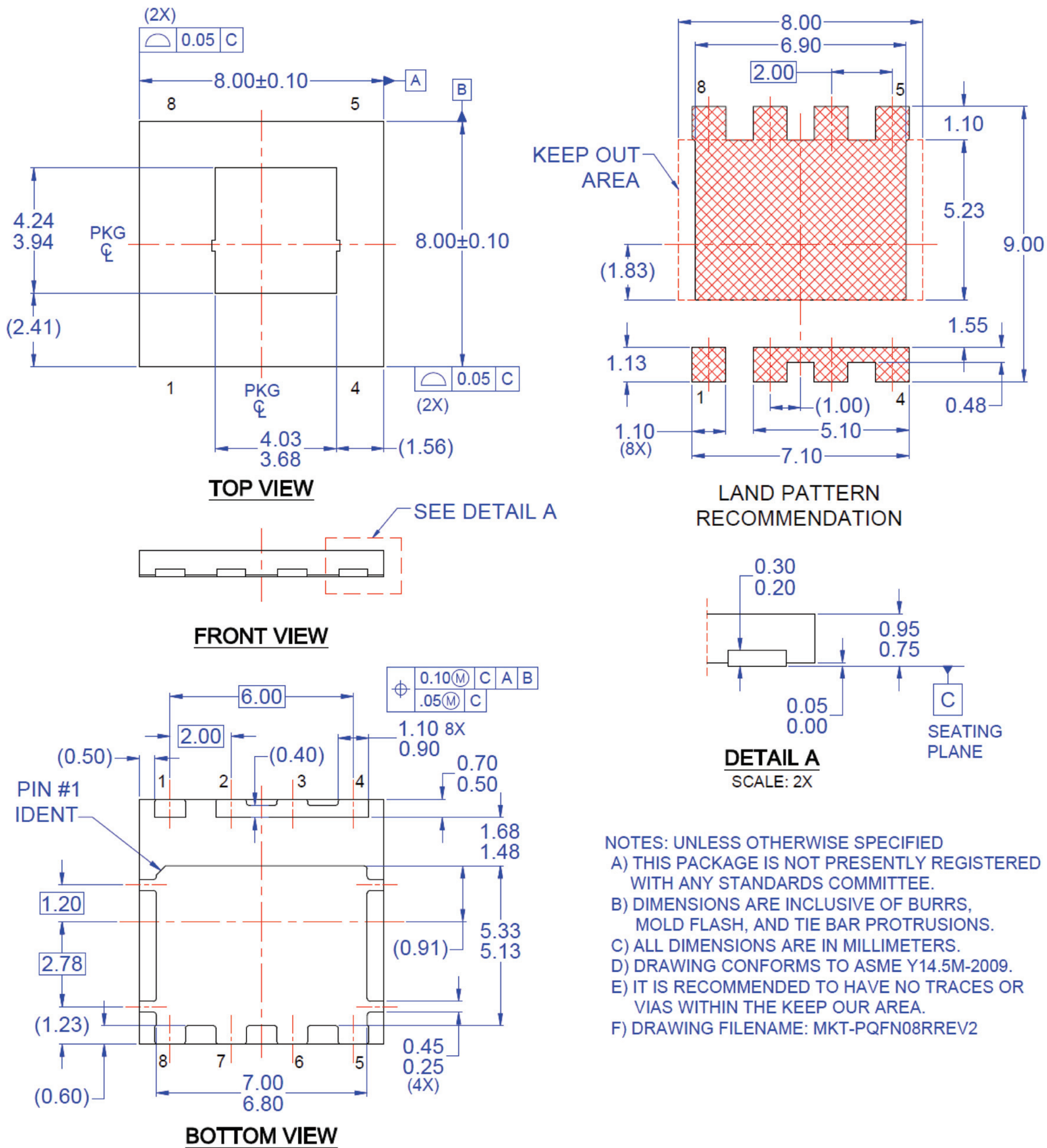


Figure 13. Junction-to-Case Transient Thermal Response Curve

Dimensional Outline and Pad Layout



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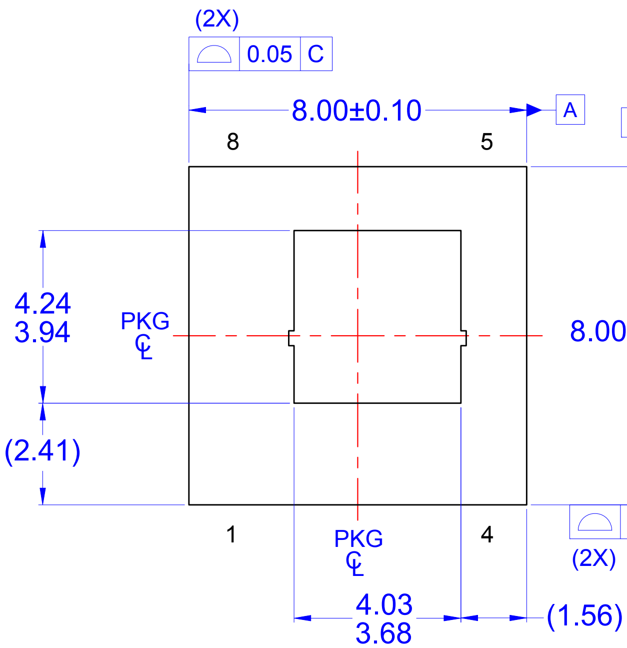
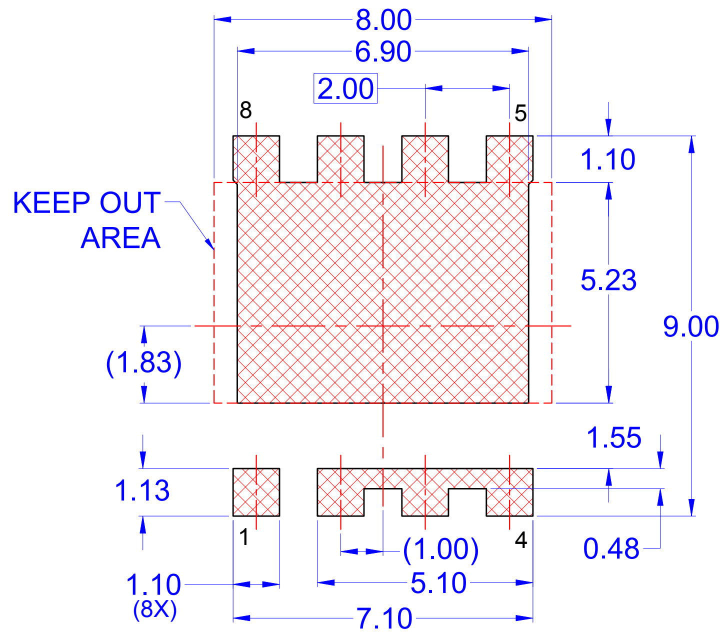
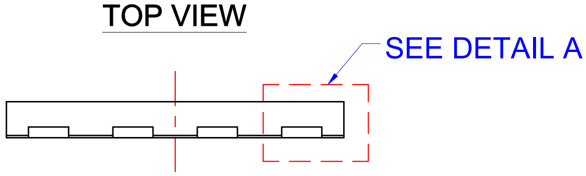


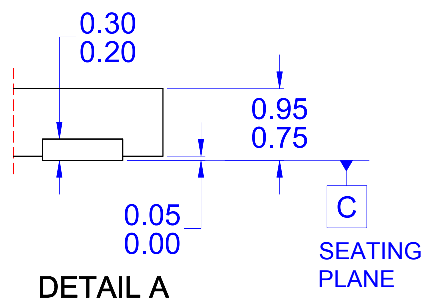
TOP VIEW



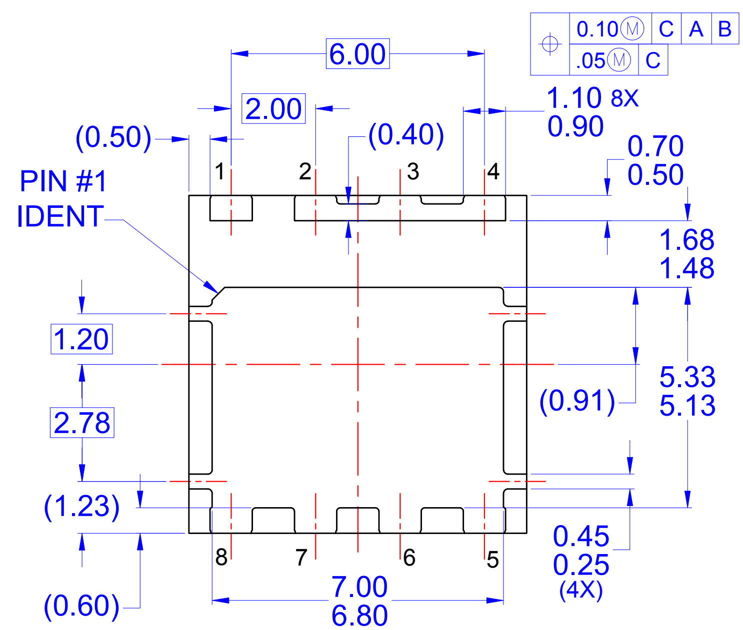
LAND PATTERN RECOMMENDATION



FRONT VIEW



DETAIL A
SCALE: 2X



BOTTOM VIEW

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